



Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

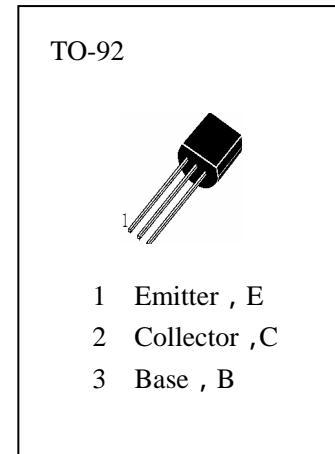
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APPLICATIONS

Class-B video output stages in colour television and professional monitor equipment

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ C$)

T_{stg}	—Storage Temperature.....	-55~150
T_j	—Junction Temperature.....	150
P_C	—Collector Dissipation.....	830mW
V_{CBO}	—Collector-Base Voltage.....	-300V
V_{CEO}	—Collector-Emitter Voltage.....	-300V
V_{EBO}	—Emitter-Base Voltage.....	-5V
I_C	—Collector Current.....	-50mA



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

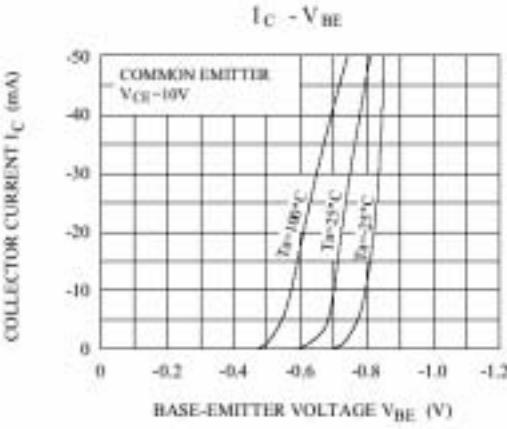
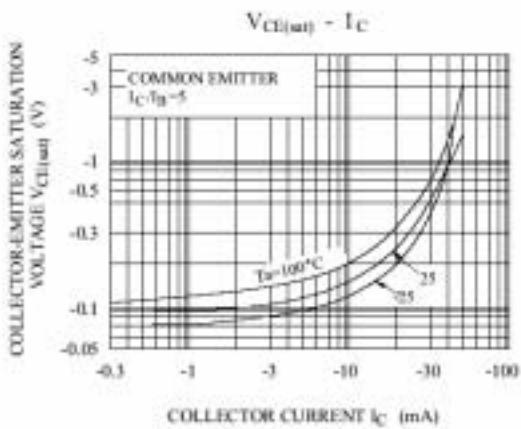
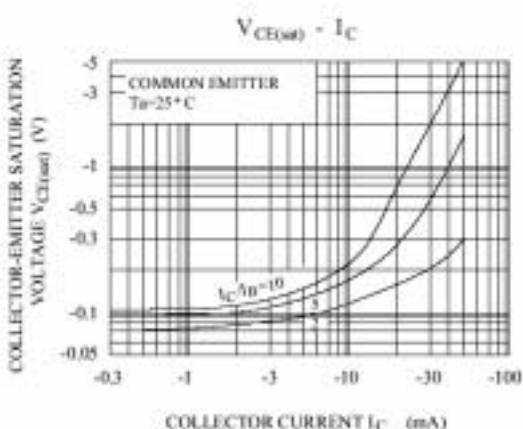
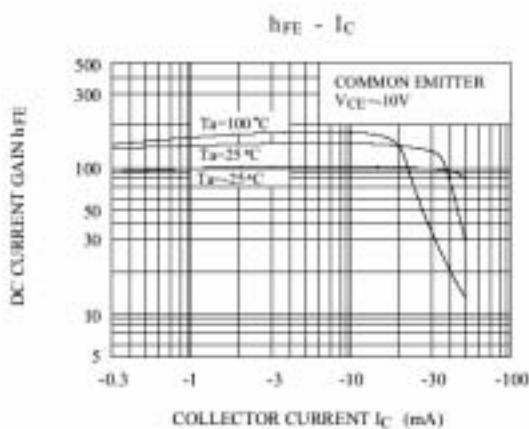
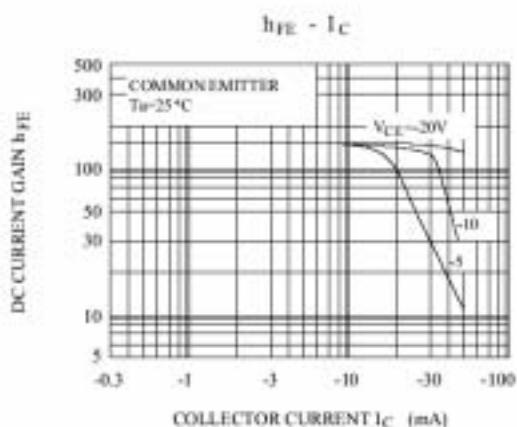
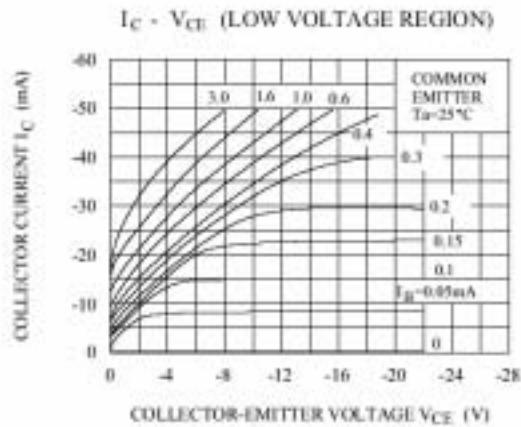
Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	-300			V	$I_C=-100 \mu A, I_E=0$
BV_{CER}	Collector-Emitter Breakdown Voltage	-300			V	$I_C=-1mA, R_{BE}=2.7K$
BV_{EBO}	Emitter-Base Breakdown Voltage	-5			V	$I_E=-10 \mu A, I_C=0$
I_{CER}	Collector Cut-off Current			-10	μA	$V_{CE}=-200V, R_{BE}=2.7$
I_{EBO}	Emitter-Base Cut-off Current			-10	μA	$V_{EB}=-5V, I_C=0$
HFE	DC Current Gain	50				$V_{CE}=-20V, I_C=-25mA$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			-0.6	V	$I_C=-30mA, I_B=-5mA$
f_T	Current Gain-Bandwidth Product	60			MHz	$V_{CE}=-10V, I_C=-10mA$
C_{ob}	Output Capacitance			1.6	pF	$V_{CB}=-30V, I_C=0, f=1MHz$



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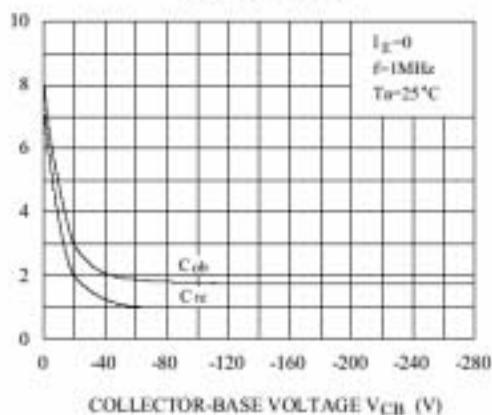
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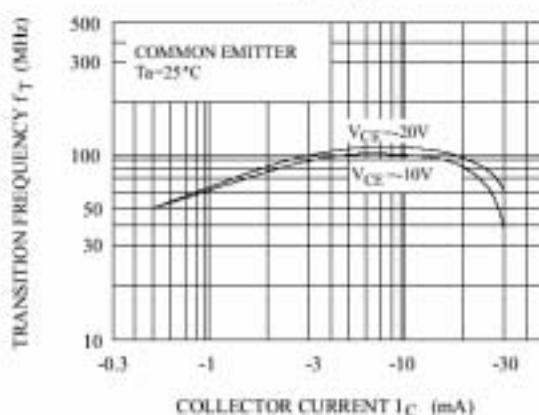
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COLLECTOR OUTPUT CAPACITANCE C_{ob} (μF)
REVERSE TRANSFER CAPACITANCE C_{re} (μF)

$C_{ob}, C_{re} - V_{CB}$

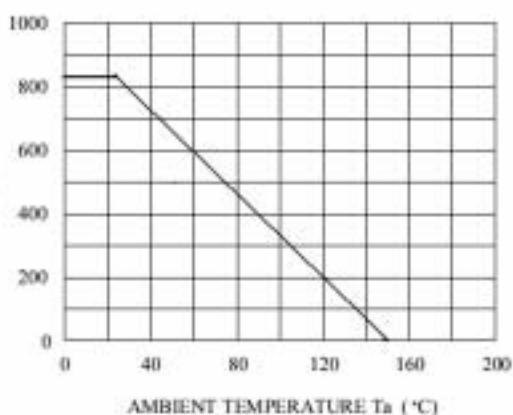


$f_T - I_C$



COLLECTOR POWER DISSIPATION
 $P_C - T_a$

$P_C - T_a$



SAFE OPERATING AREA

